

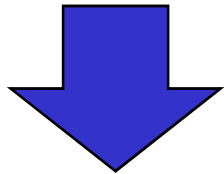
# Development of FPCCD Readout ASIC

'07 10/25 Y. Takubo  
(Tohoku university)

# Introduction

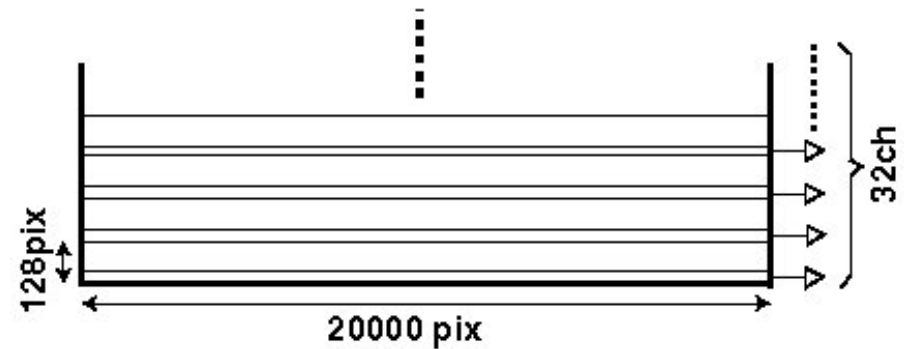
## FPCCD vertex detector

- Pixel size :  $5\mu\text{m}$
- Thickness :  $15\mu\text{m}$
- Signal level :  $\sim 500e$  for large angle
- Readout channel : 16 or 32 ch
  - $\sim 20,000 \times 128$  pix/ch

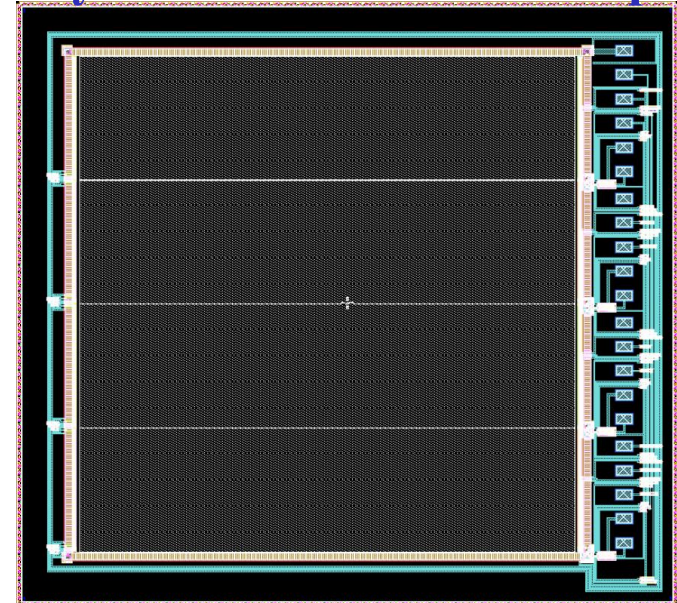


**Test-sample will be delivered in the end of 2007.**

- Pixel size :  $12\mu\text{m}$
- Readout channel : 4ch
  - $512 \times 128$  pix/ch



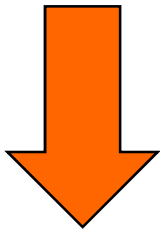
**Layout of FPCCD test-sample**



# Motivation to develop readout ASIC

## Motivation to develop readout ASIC

- The FPCCD test-sample will be delivered in the end of this year.
- The FPCCD has a large number of readout pixels.
  - Test sample : 512 x 128 pix/ch
- There is no readout ASIC suitable for the FPCCD.



**Readout ASIC for the FPCCD is necessary.**

- For FPCCD test-sample
- To establish readout technique

# Requirement to the readout ASIC

## Requirement to the readout ASIC

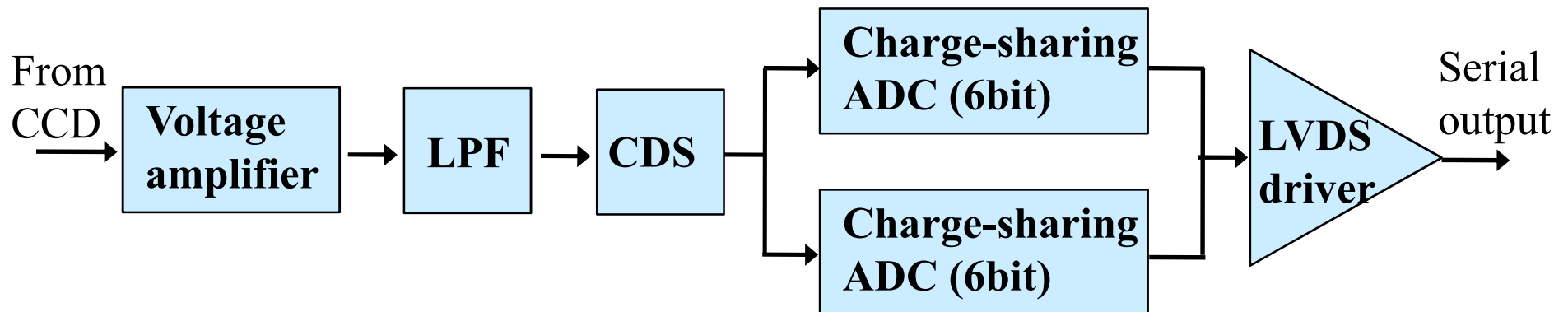
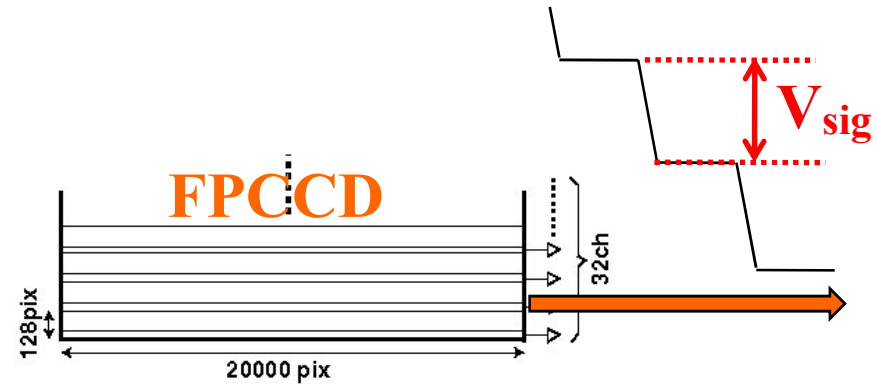
- All elements to operate and read FPCCD are contained in one chip.
- **Readout rate :  $>10$  Mpix/sec**
  - $[20000 \times 128 \text{ pix}]/[0.2 \text{ s}]$
- **Noise level of the ASIC :  $< 30$  electrons**
  - Required total noise level including the CCD :  $<50$  electrons
  - Noise level of FPCCD :  $\sim 30$  electrons
- **Power consumption :  $< 6$  mW/ch**
  - The power consumption in a cryostat should be  $<100$  W.
  - Required total power consumption :  $<16$  mW/ch ( $\sim 100\text{W}/6000\text{ch}$ )
  - CCD :  $\sim 10\text{mW}/\text{ch}$

To achieve these requirement, readout ASIC is designed.

# Design concept of readout ASIC

## ASIC elements

- Voltage amplifier
- LPF (Low-pass filter)
- CDS (Correlated double sampling)
- ADC
  - 2 charge sharing ADC are used alternatively to achieve 10Mpix/sec.
- LVDS driver

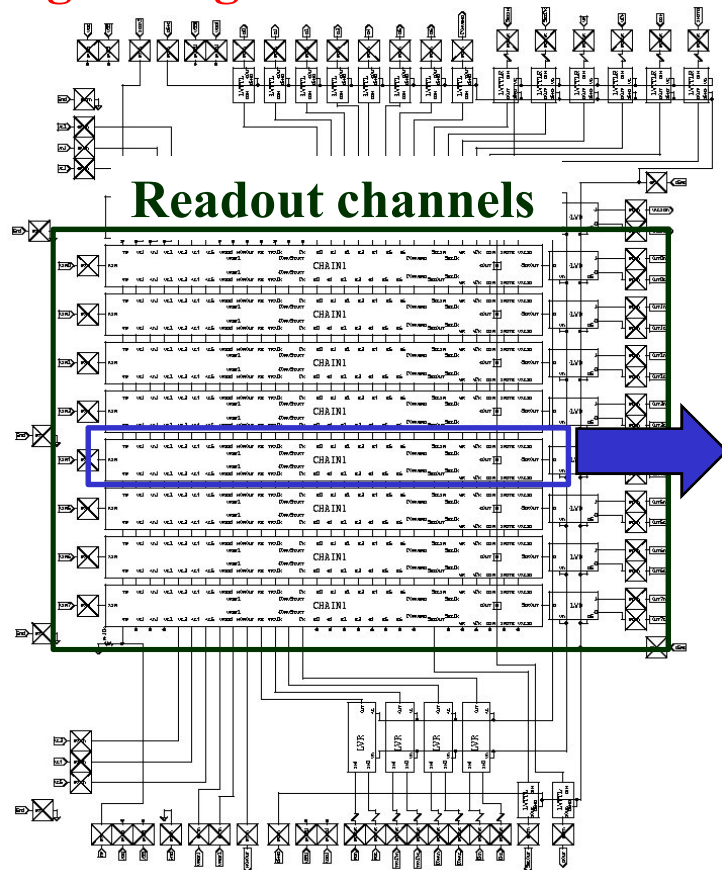


The design was optimized with SPICE simulation.

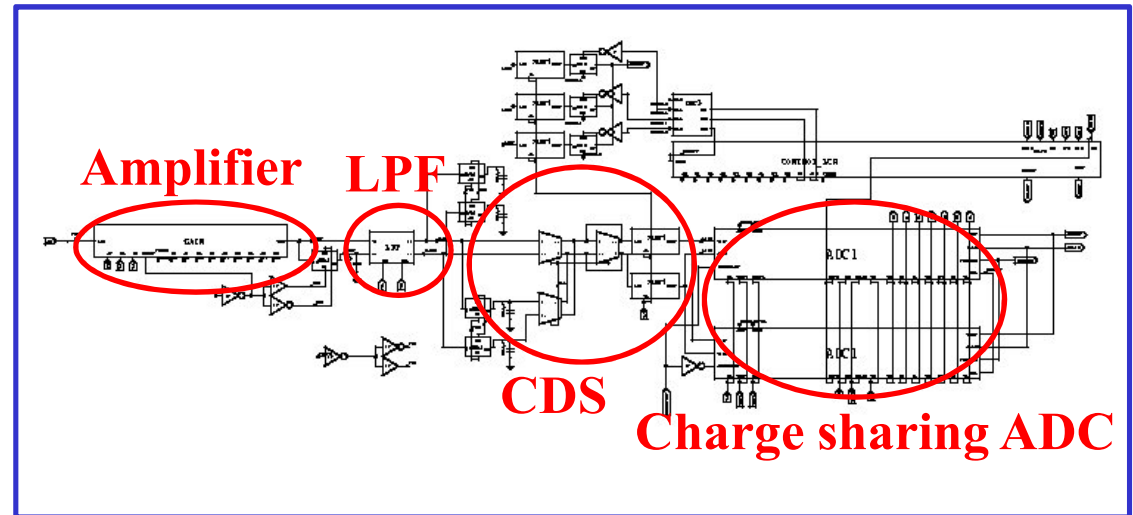
# Design optimization with SPICE

- The SPICE simulation was applied to design the readout ASIC.
- The design was optimized for 0.35  $\mu\text{m}$  process by TSMC.

## Logic design of the readout ASIC



## Logic design of the readout channels

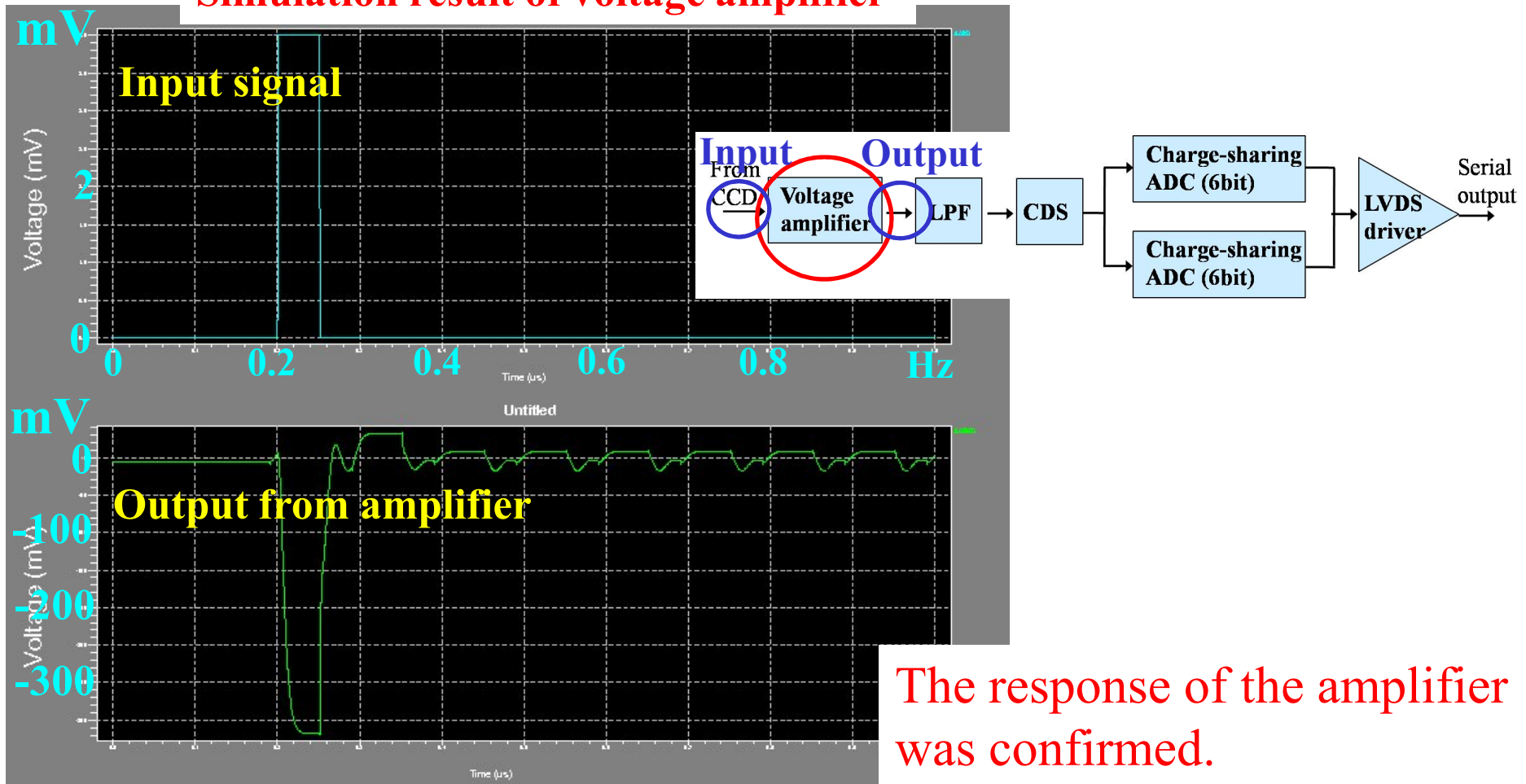


Each elements were check with simulation.

# Voltage amplifier

- The amplifier was designed to have the gain of 10~100.
- The gain can be adjustable by changing bias current.

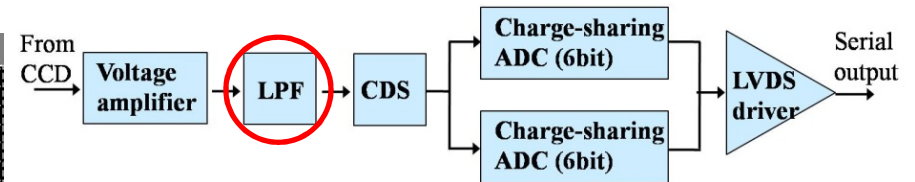
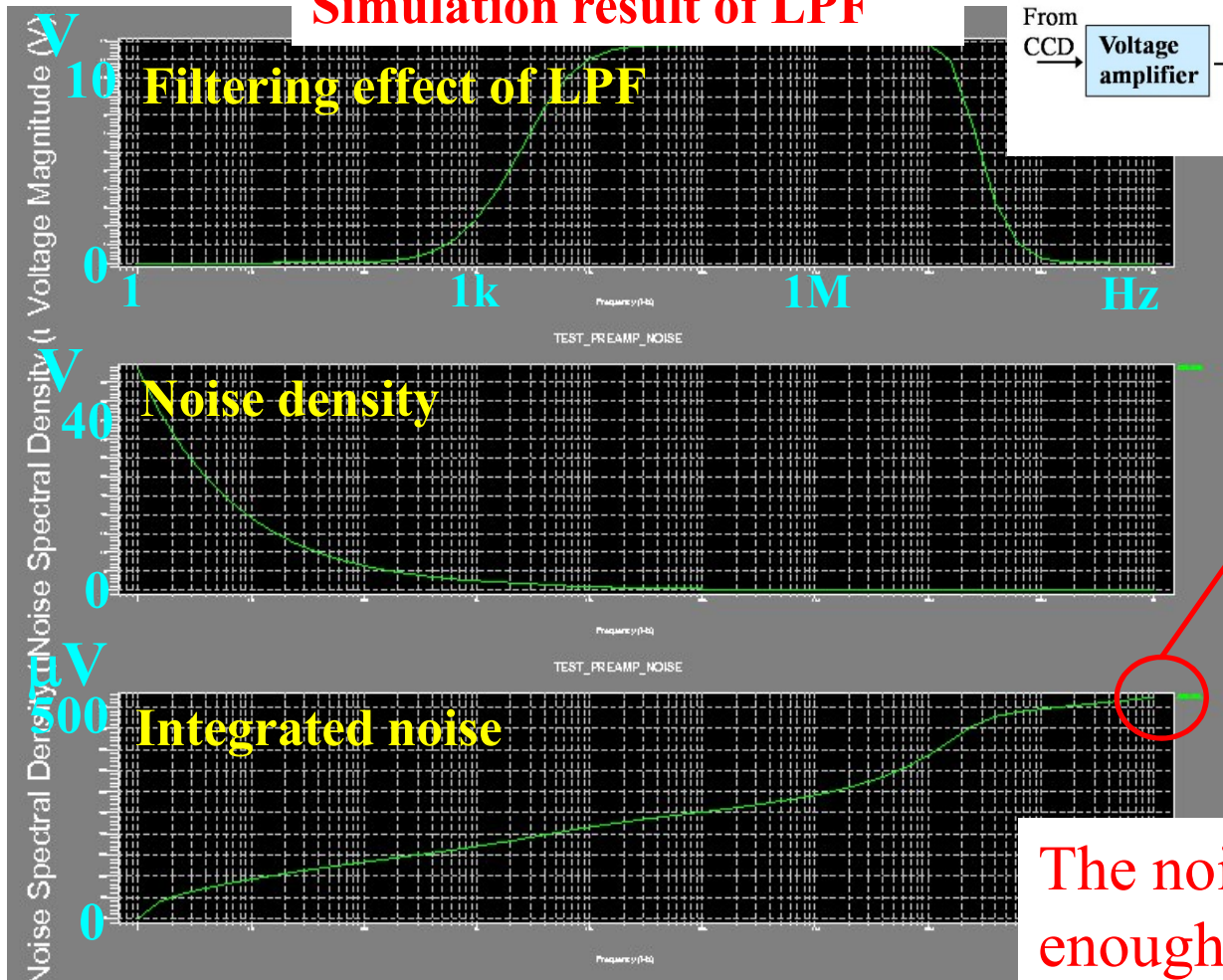
## Simulation result of voltage amplifier



# Low Pass Filter

- Response of the LPF was investigated by noise analysis of SPICE.
- Adjustability of band-width was checked.

## Simulation result of LPF



## Initial noise level

$$\sim [500\mu\text{V}]/[50\text{V}/e]$$

$$\sim 10 e$$

- Voltage gain :  $50\mu\text{V}/e$

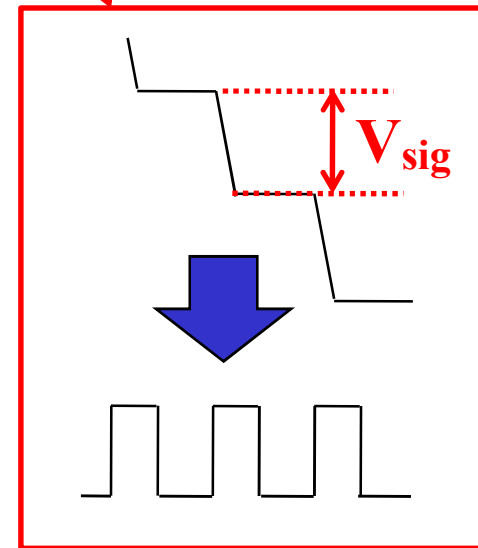
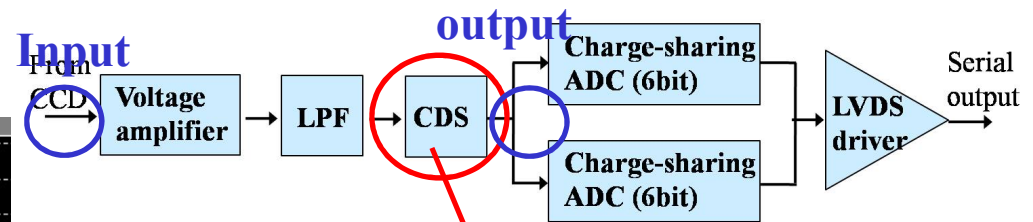
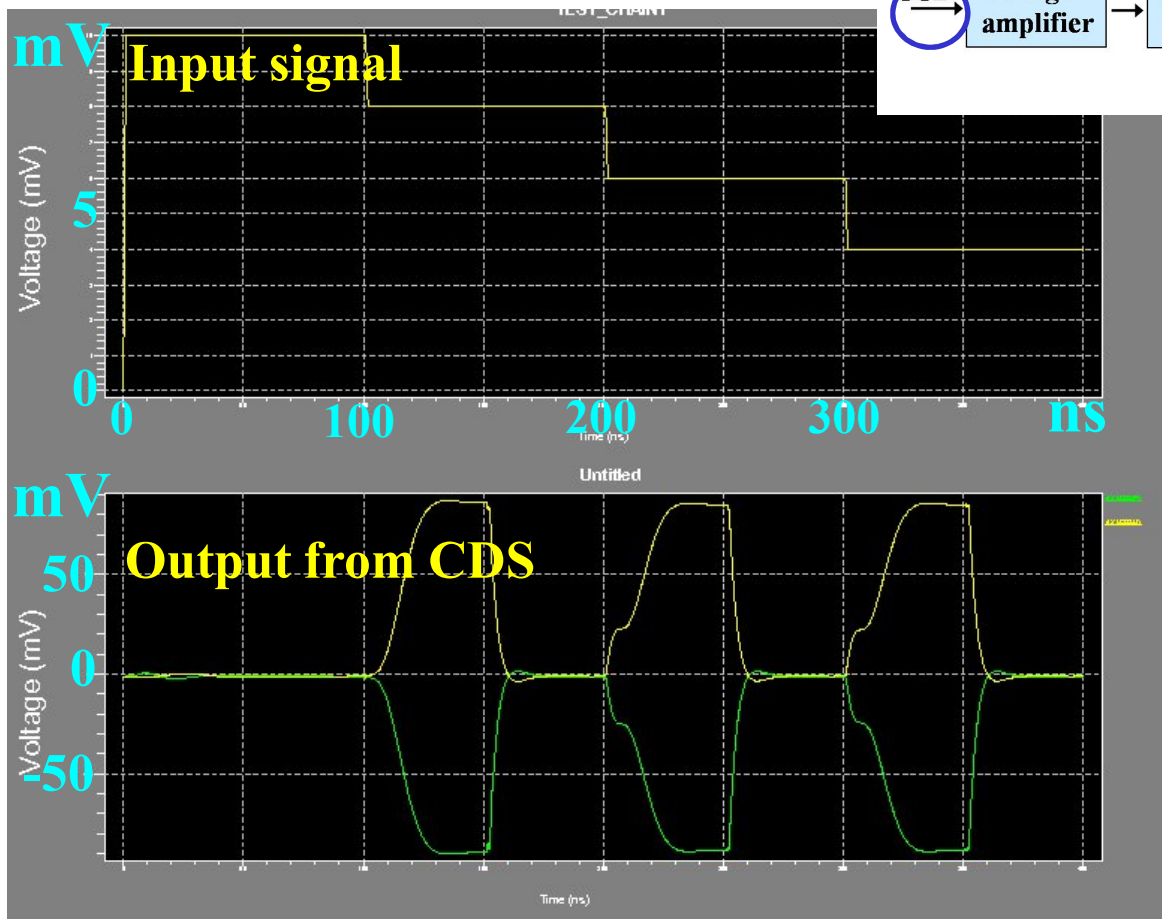
The noise level is expected to be enough below our requirement.



# Correlated double sampling circuit

CDS obtains the voltage difference corresponding to charges contained in one pixel.

Simulation result of CDS

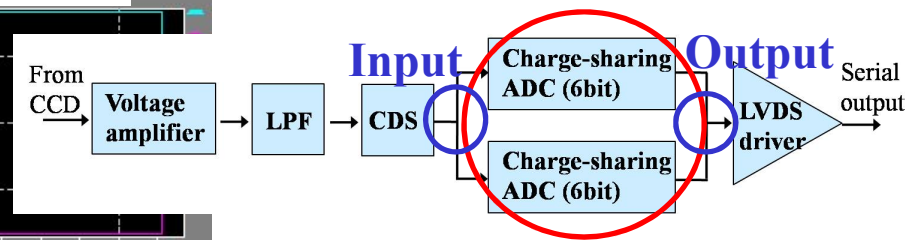
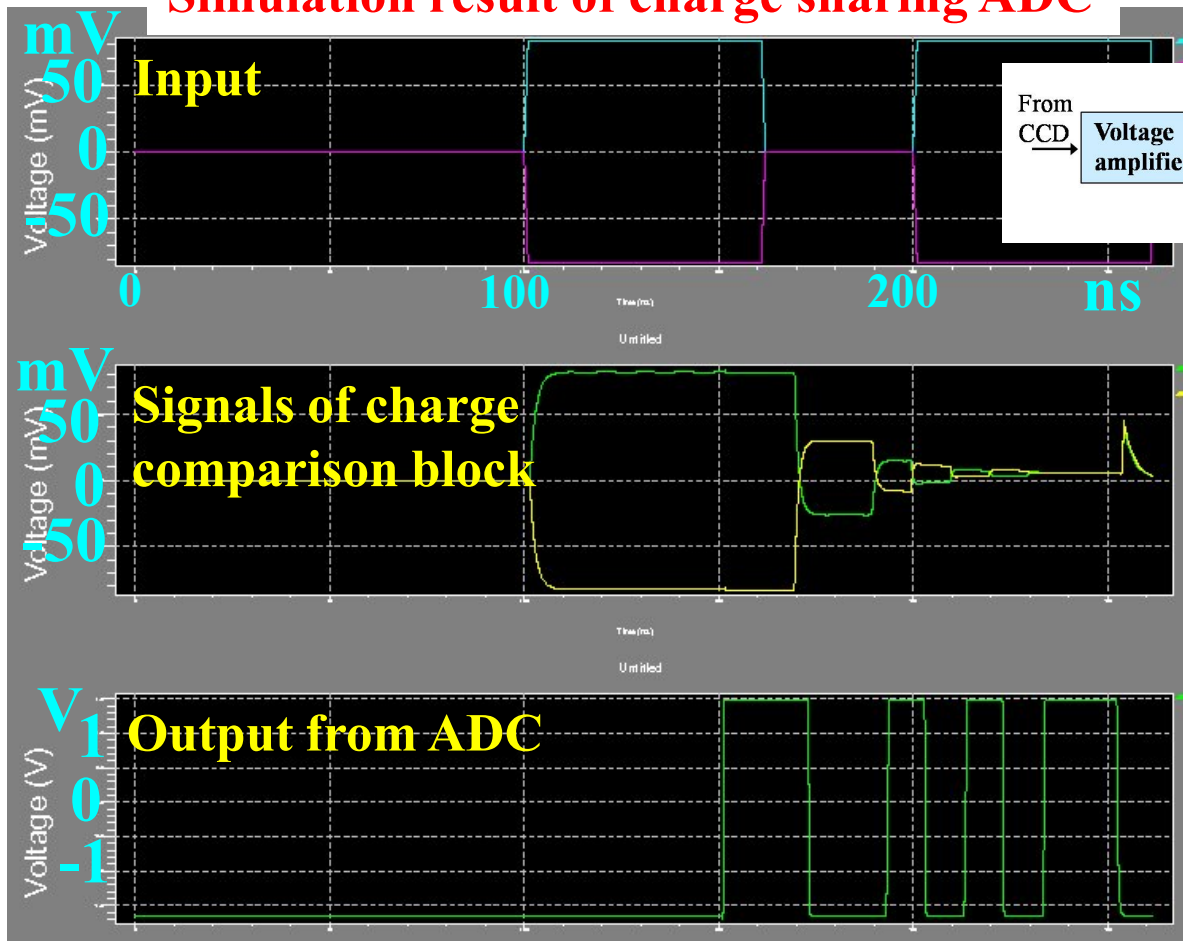


CDS circuit work correctly.

# Charge sharing ADC

Charge sharing ADC performs A/D conversion, comparing stored charges in capacitors.

## Simulation result of charge sharing ADC



A/D conversion can be performed with 10MHz.

Response of all ASIC elements was confirmed.

# Expected performance

## Expected performance

- Readout rate : 10 Mpix/sec **→ OK!**
  - Data conversion rate : 10MHz (= 5x2 MHz)
  - 260 ms/ch : [20000 x 128 pix/ch] x [10<sup>-7</sup> s/pix]
- Power consumption < 5 mW/ch **→ OK!**
  - Charge-sharing ADC realizes low power. (~10 μW)
- Noise level : ~10e **→ OK!**
  - Estimation with SPICE simulation.

**The performance will satisfy our requirement.**

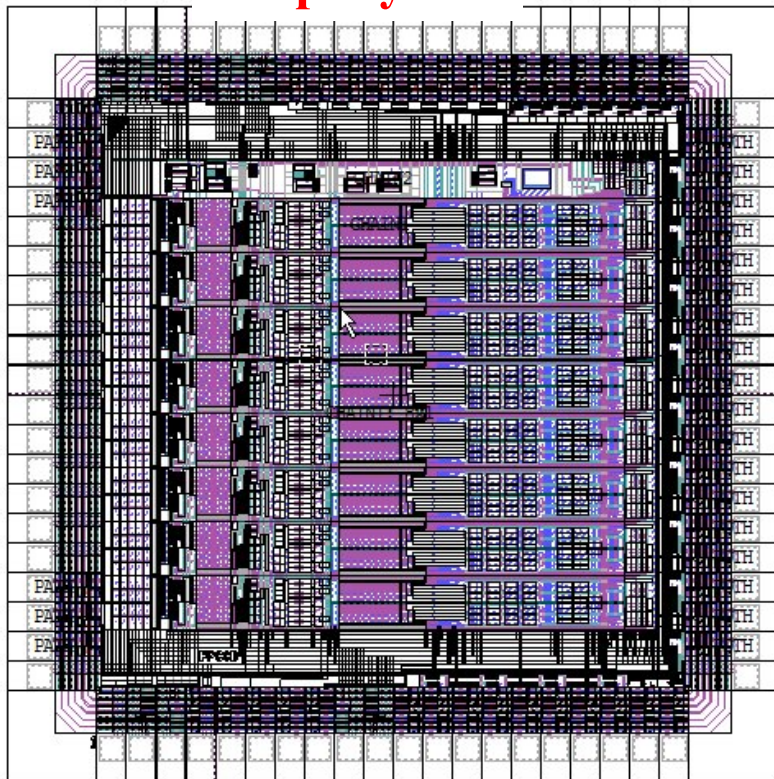


ASIC layout was ordered to a company (Digian technology).

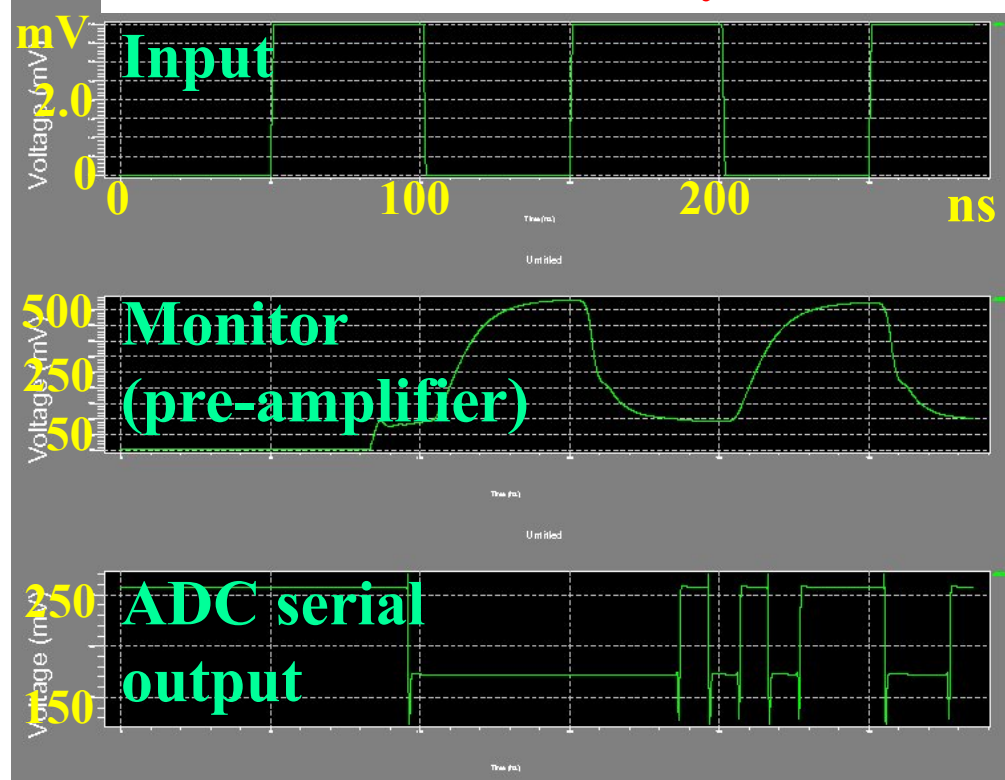
# Layout check

- ASIC layout made by a company was checked.
  - SPICE simulation was performed with layout data.
- ➔
- The production was ordered to MOSIS.
  - **The ASIC will be delivered on Dec.**

**Chip layout**



**SPICE simulation with layout data**



# Specification of readout ASIC

## Specification of readout ASIC

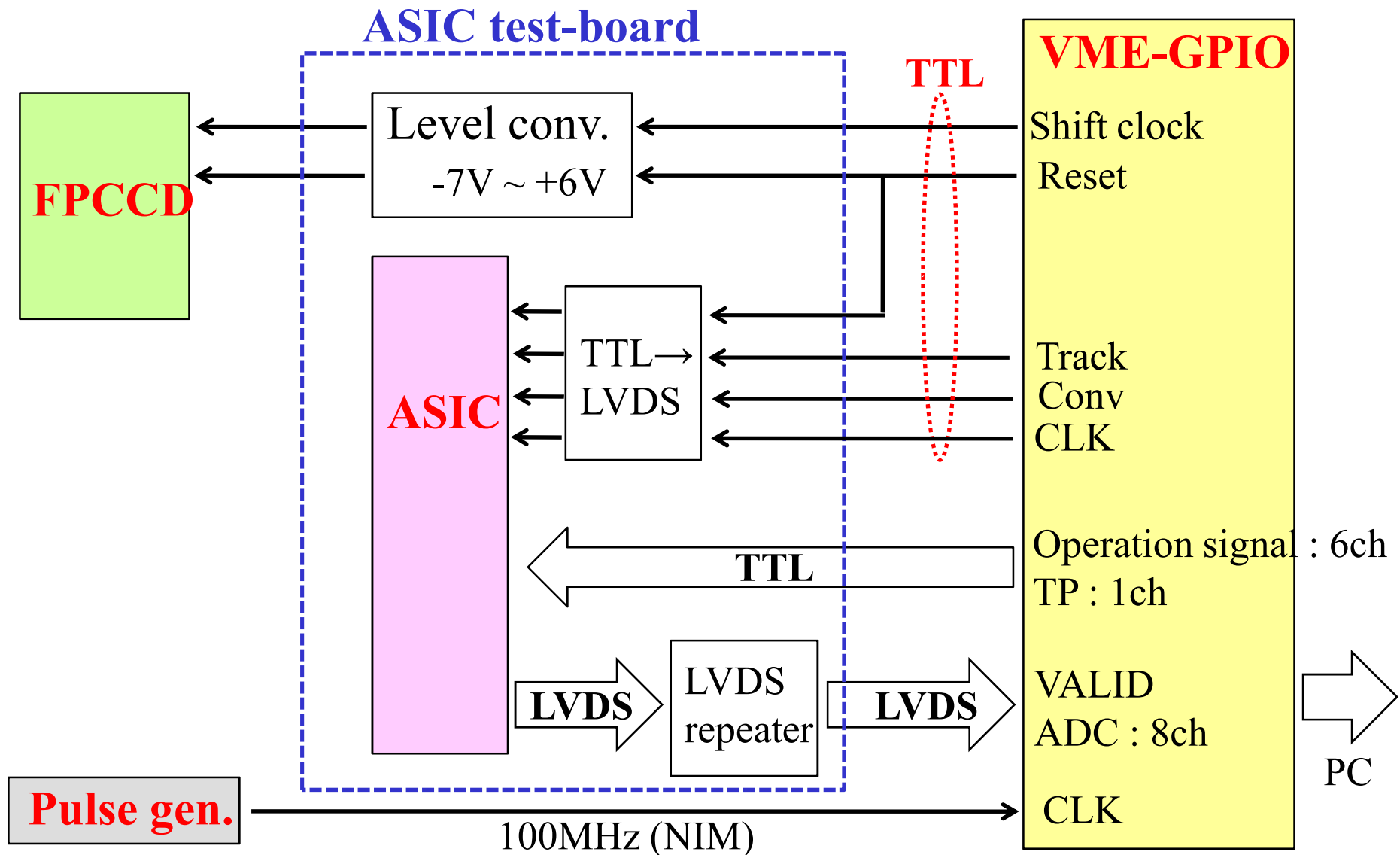
- 0.35  $\mu\text{m}$  process by TSMC
- Size : 2.85 x 2.85 mm<sup>2</sup>
- # of pad : 80
- # of signal channels : 8
- AD conversion rate : 10 MHz (=5MHz x 2)
- Clock frequency : 100 MHz
- Data width : 6bit + sign bit
- Power rail :  $\pm 1.65$  V
- Analog gain : adjustable
- Frequency bandwidth : adjustable
- Interface : LVDS/LVTTL

# Summary

- Development of readout ASIC for FPCCD was started.
- The ASIC design was optimized with SPICE simulation.
  - The performance will satisfy our requirements.
- The layout was made by a company (Digian technology).
  - The response was checked by SPICE simulation with layout data.
- The readout ASIC will be delivered on December.



# Block diagram of Test-bench

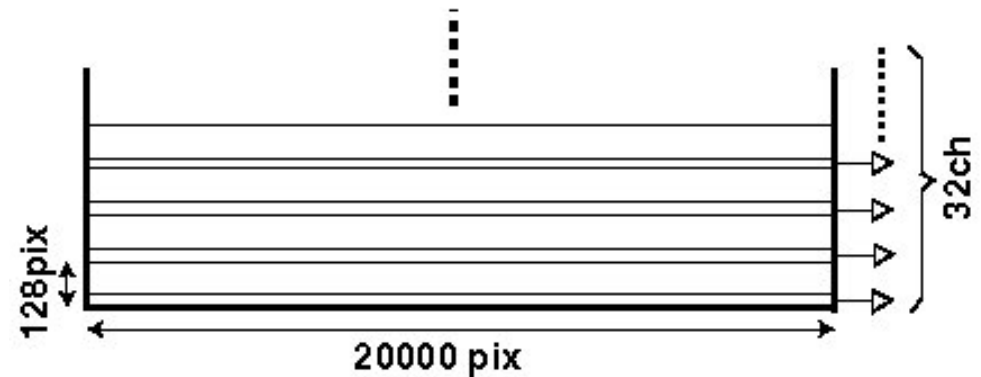




# ILC-FPCCD

## ILC-FPCCD

- Pixel size :  $5\mu\text{m}$
- Thickness :  $15\mu\text{m}$
- Signal level :  $\sim 500e$  for penetration with large angle  
→ Readout ASIC must be low noise.
- Wafer size
  - L1, L2 :  $10 \times 65 \text{ mm}^2$
  - L3-L6 :  $20 \times 100 \text{ mm}^2$
- Readout channel : 16 or 32 ch
  - L1, L2 :  $13,000 \times 128 \text{ pix/ch}$
  - L3-L6 :  $20,000 \times 128 \text{ pix/ch}$

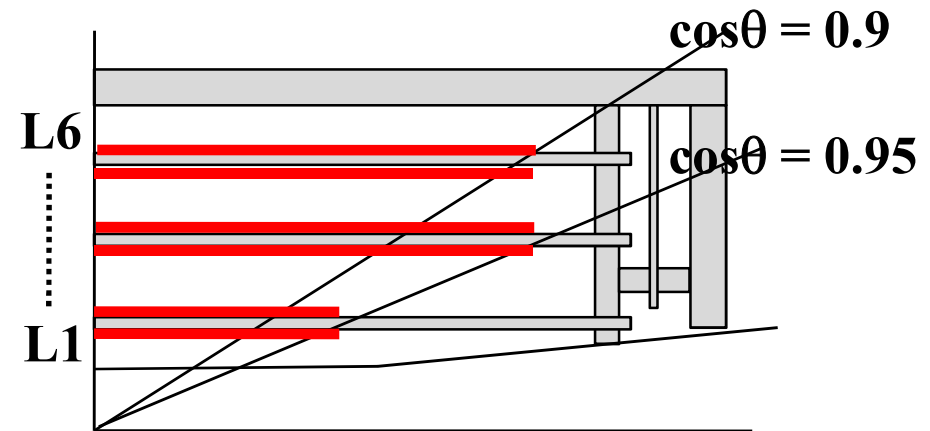


ILC vertex detector is constructed with FPCCD wafers.

# FPCCD vertex detector

## FPCCD vertex detector

- # of wafers : 220
- Readout channel : ~6000ch
- All pixels in one channel is read within 200ms
- Required power consumption : < 100W.
  - to be investigated



	Size (mm <sup>2</sup> )	ch/wafer	# of wafers	# of ch
<b>L1, L2</b>	10 x 65	16	15( $\phi$ ) x 2(z)	480
<b>L3, L4</b>	20 x 100	32	16( $\phi$ ) x 2(z)	1024
<b>L5, L6</b>	20 x 100	32	24( $\phi$ ) x 2(z)	1536
<b>Total</b>			220	6080

Structure and performance of FPCCD determines requirement to the readout ASIC.